

EUROPEAN PATENT OFFICE

Patent Abstracts of Japan

PUBLICATION NUMBER : 01232695
PUBLICATION DATE : 18-09-89

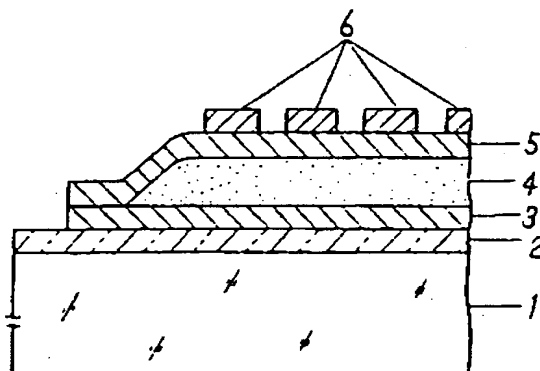
APPLICATION DATE : 11-03-88
APPLICATION NUMBER : 63058748

APPLICANT : MATSUSHITA ELECTRIC IND CO LTD;

INVENTOR : ABE ATSUSHI;

INT.CL. : H05B 33/22 G09F 9/30

TITLE : THIN FILM ELECTROLUMINESCENT
ELEMENT



ABSTRACT : PURPOSE: To make adhesion between thin films good and let luminescence characteristics maintained stably for a long period by composing a dielectric layer of a composite thin film of AlN to which BN is added.

CONSTITUTION: A thin film of indium-tin mixed crystal oxide is formed on a glass substrate 1 by sputtering and processed into stripes by photo-etching to be a transparent electrode 2. A first layer of dielectric 3 is formed on it by sputtering consisting of AlN solely or AlN including BM, and a fluorescent thin film 4 of ZnS:Mn is formed by EB deposition. A second layer of dielectric 5 is then formed in the completely similar method to that for the layer 3, and finally a back electrode 6 of Al is applied by EB deposition, which are then processed to be perpendicular stripes to the electrode 2. A thin film electroluminescent element having a good peeling resistance, good withstand voltage characteristics and extremely small fluctuation of luminescence threshold voltage in drive for a long time can thus be manufactured at a good yield.

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